

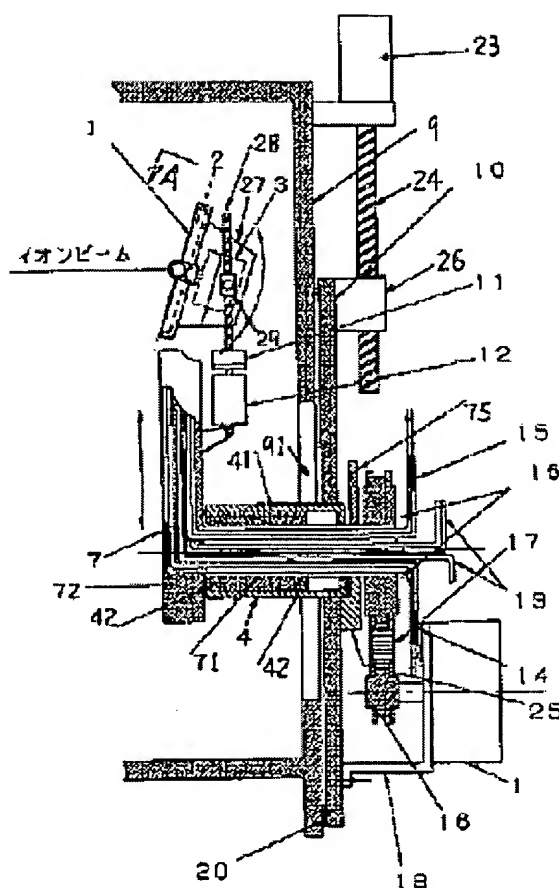
ION IMPLANTER

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Inventor: HIDAKA YOSHITOMO; OKADA KEIJI
Applicant: SUMITOMO EATON NOBA KK
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- international: H01J37/317; H01L21/265
- european:
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Abstract of JP11007915

PROBLEM TO BE SOLVED: To provide an ion implanter of a sheet capable of uniformly implanting ions to a semiconductor wafer with an emitting direction of an ion beam fixed.

SOLUTION: An emitting direction of an ion beam is fixed. Ions are implanted to a semiconductor wafer 1 while the semiconductor wafer 1 is mechanically moved laterally and vertically. For this purpose, an oscillating mechanism is provided for reciprocally and laterally moving a wafer platen 2, which holds the semiconductor wafer 1 therein, at a constant speed inside a vacuum container 9, and a vertically driving mechanism is provided for vertically moving the wafer platen 2 at another constant speed.



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